

Client's ref: toppoly P91156/羅平
File:0773-9139USF/Jacky/Steve
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ABSTRACT OF THE DISCLOSURE

A method of forming a CMOS TFT device. The present method features that the n^+ -ion doping procedure is performed after defining the contact holes located in the doped areas. Thus,
5 the source/drain region of the NMOS can be formed. The present invention requires only five photomasks, thereby reducing the number of photomasks consumed in the prior art.